

VZ Series Power MOSFET

N-Channel Enhancement type

2SK2560

(F20F20VZ)

200V 20A

FEATURES

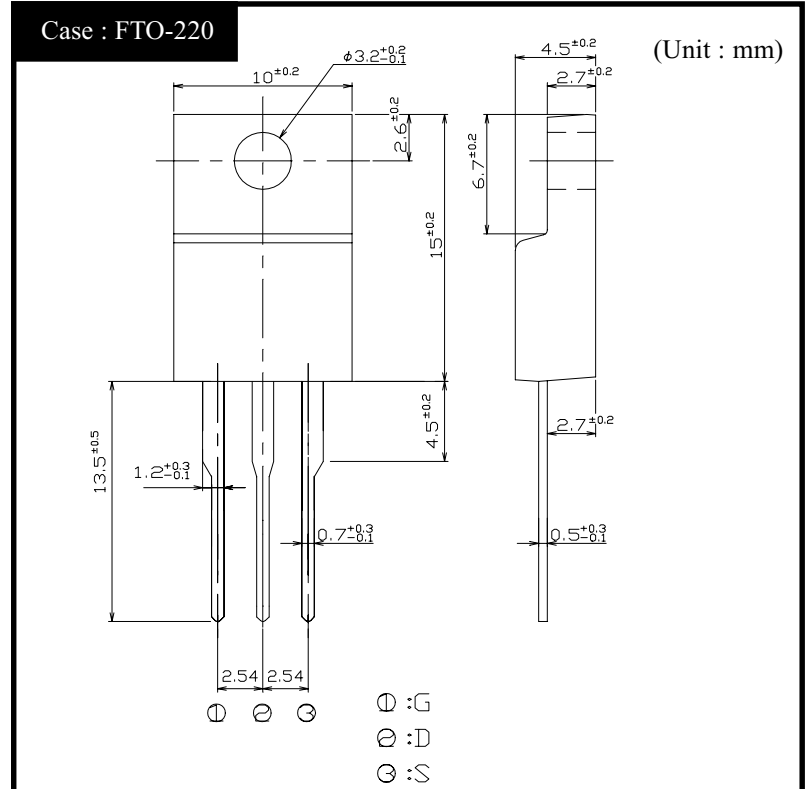
- Input capacitance (C_{iss}) is small. Especially, input capacitance at 0 bias is small.
- The static $R_{ds(on)}$ is small.
- The switching time is fast.

APPLICATION

- DC/DC converters
- Power supplies of DC 12-24V input
- Product related to Integrated Service Digital Network

OUTLINE DIMENSIONS

Case : FTO-220



RATINGS

- Absolute Maximum Ratings (Tc = 25°C)

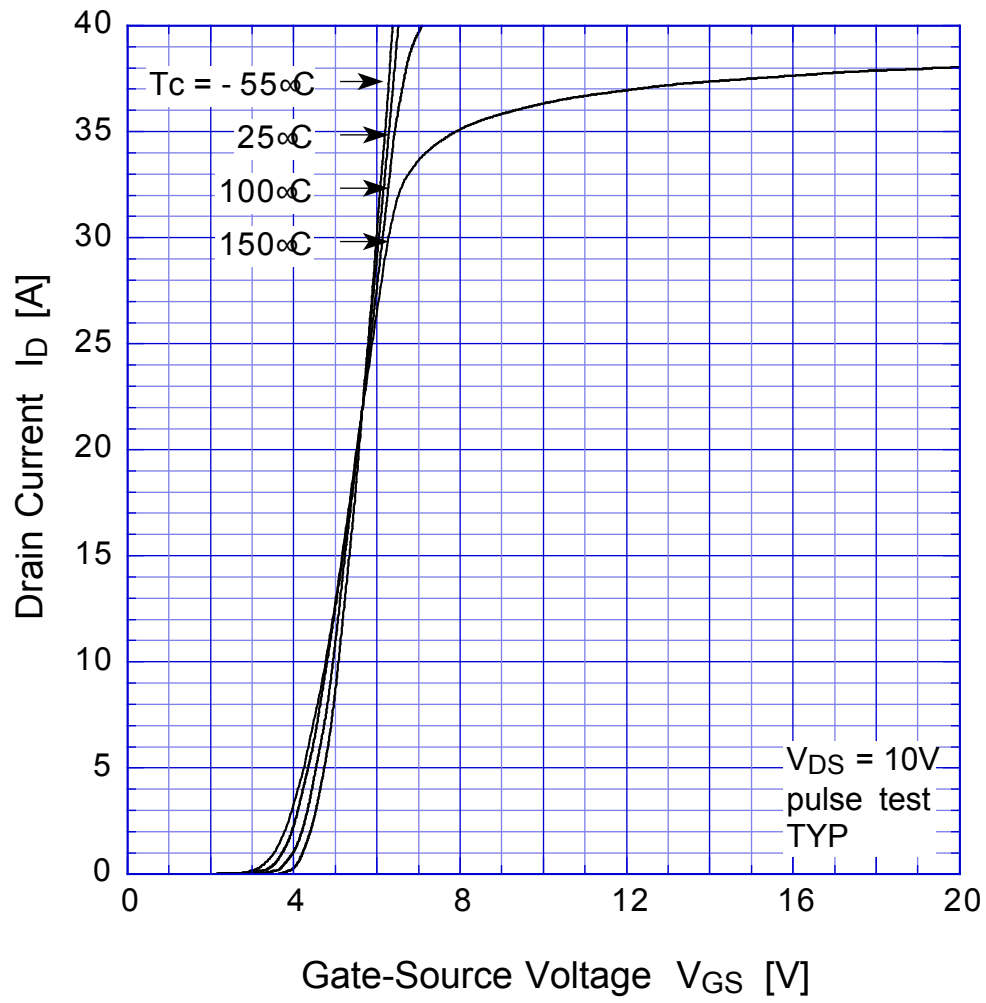
Item	Symbol	Conditions	Ratings	Unit
Storage Temperature	T_{stg}		-55~150	°C
Channel Temperature	T_{ch}		150	
Drain-Source Voltage	V_{DSS}		200	V
Gate-Source Voltage	V_{GSS}		±30	
Continuous Drain Current (DC)	I_D		20	A
Continuous Drain Current (Peak)	I_{DP}		40	
Continuous Source Current (DC)	I_S		20	
Total Power Dissipation	P_T		60	W
Single Pulse Avalanche Current	I_{AS}	$T_{ch} = 25^{\circ}\text{C}$	20	A
Dielectric Strength	V_{dis}	Terminals to case, AC 1 minute	2	kV
Mounting Torque	TOR	(Recommended torque :0.3 N·m)	0.5	N·m

●Electrical Characteristics $T_c = 25^\circ\text{C}$

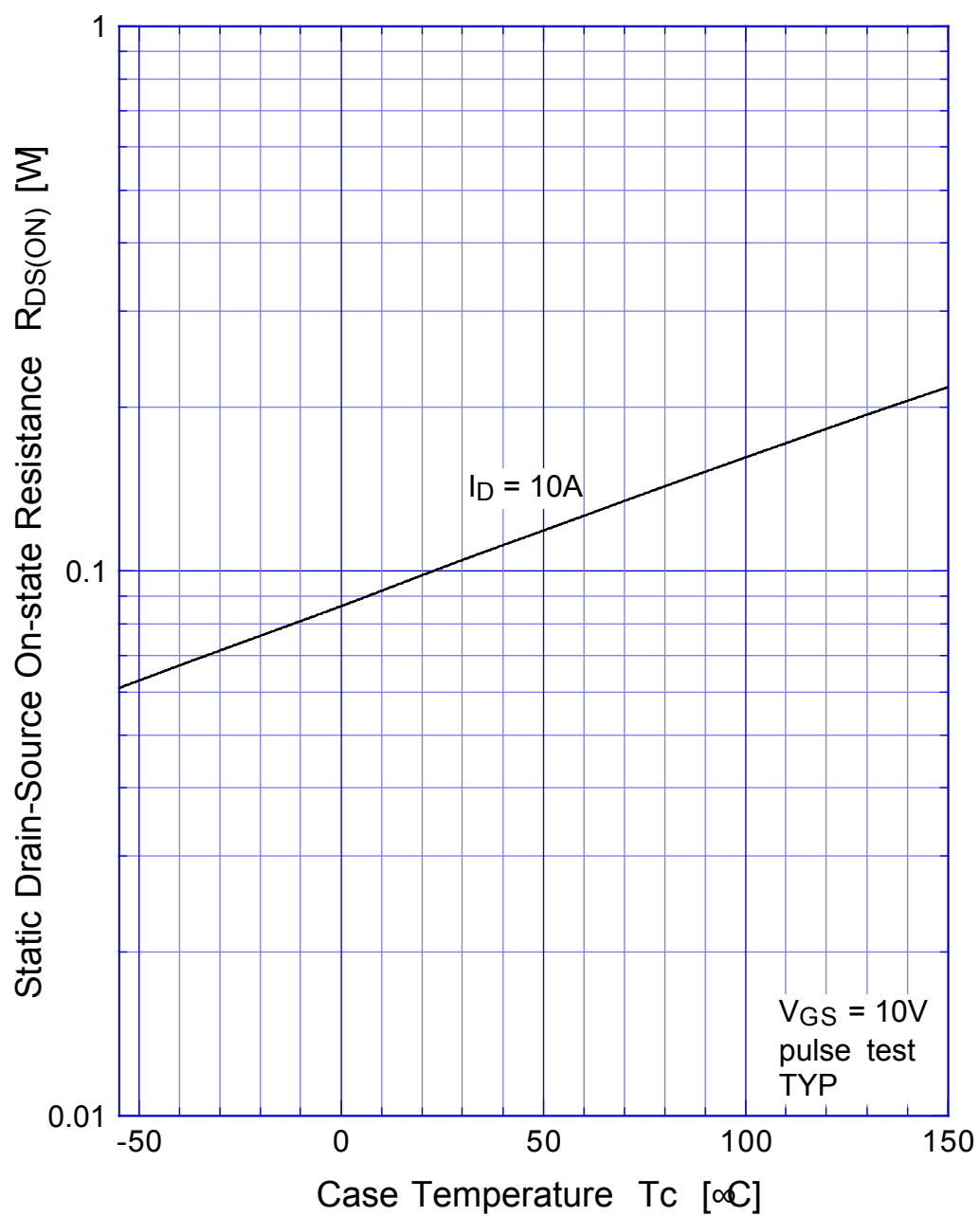
Item	Symbol	Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 1\text{mA}$, $V_{GS} = 0\text{V}$	200			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 200\text{V}$, $V_{GS} = 0\text{V}$			250	μA
Gate-Source Leakage Current	I_{GSS}	$V_{GS} = \pm 30\text{V}$, $V_{DS} = 0\text{V}$			± 0.1	
Forward Transconductance	g_{fs}	$I_D = 10\text{A}$, $V_{DS} = 10\text{V}$	7	14		S
Static Drain-Source On-state Resistance	$R_{DS(ON)}$	$I_D = 10\text{A}$, $V_{GS} = 10\text{V}$		0.1	0.18	Ω
Gate Threshold Voltage	V_{TH}	$I_D = 1\text{mA}$, $V_{DS} = 10\text{V}$	2.0	3.0	4.0	V
Source-Drain Diode Forward Voltage	V_{SD}	$I_S = 10\text{A}$, $V_{GS} = 0\text{V}$			1.5	
Thermal Resistance	θ_{jc}	junction to case			2.08	$^\circ\text{C}/\text{W}$
Total Gate Charge	Q_g	$V_{DD} = 150\text{V}$, $V_{GS} = 10\text{V}$, $I_D = 20\text{A}$		55		nC
Input Capacitance	C_{iss}	$V_{DS} = 10\text{V}$, $V_{GS} = 0\text{V}$, $f = 1\text{MHz}$		1800		pF
Reverse Transfer Capacitance	C_{rss}			165		
Output Capacitance	C_{oss}			620		
Turn-On Time	t_{on}	$I_D = 10\text{A}$, $R_L = 10\Omega$, $V_{GS} = 10\text{V}$		100	200	ns
Turn-Off Time	t_{off}			280	560	

2SK2560

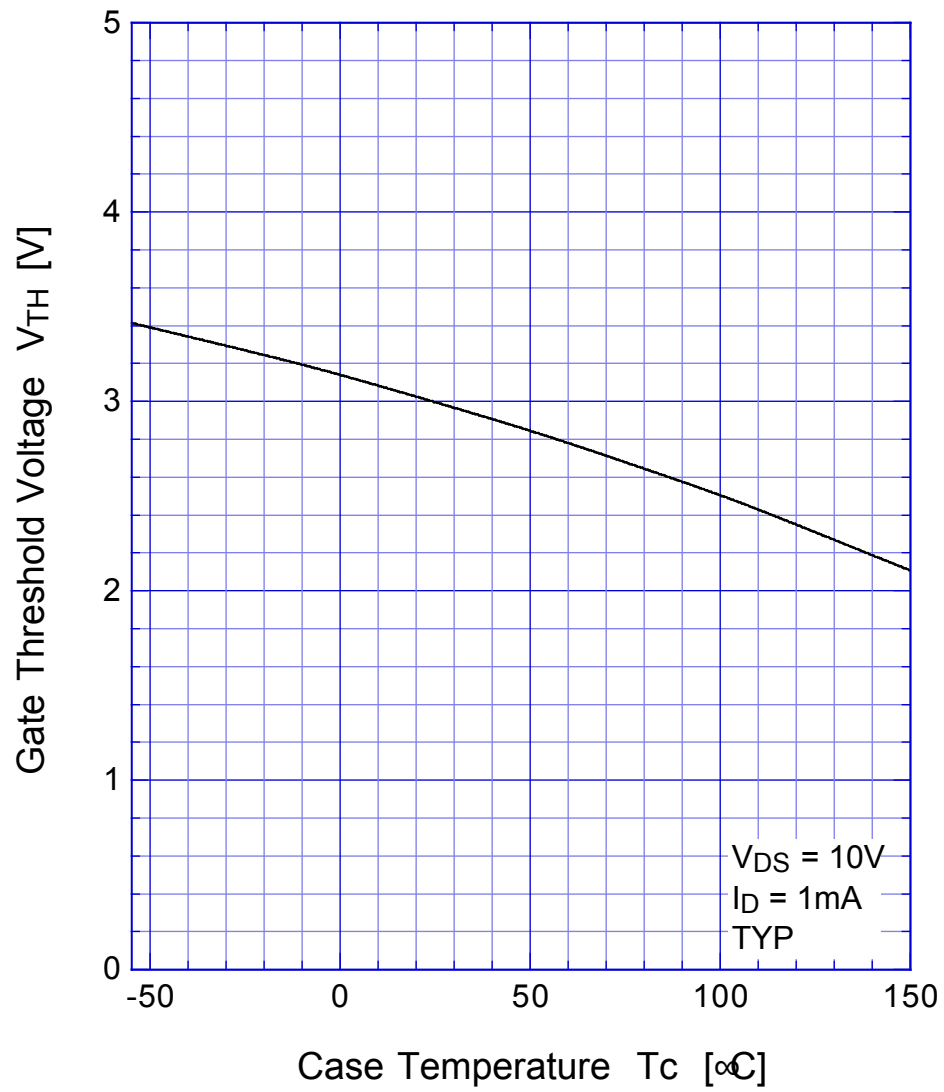
Transfer Characteristics



2SK2560 Static Drain-Source On-state Resistance

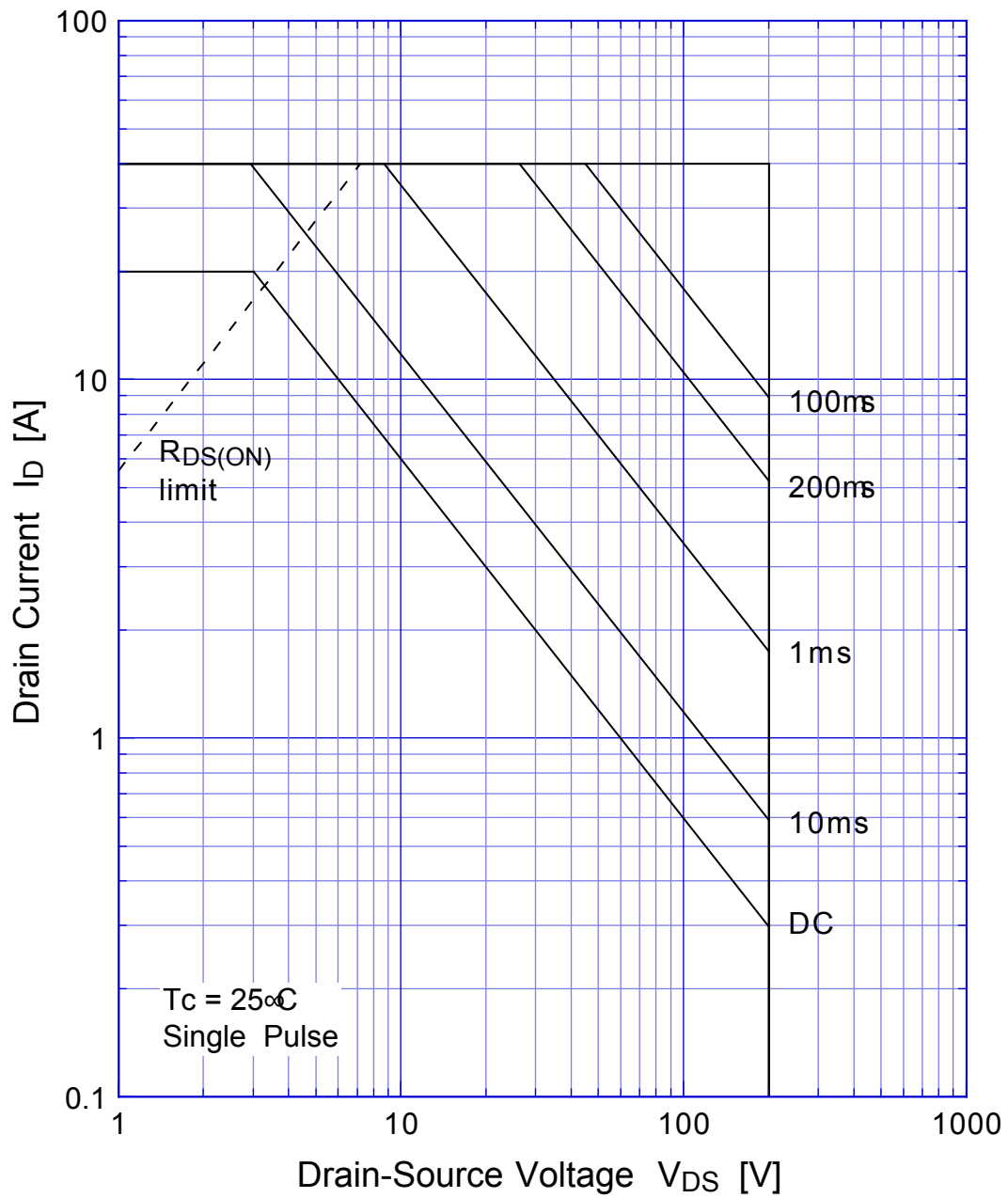


2SK2560 Gate Threshold Voltage

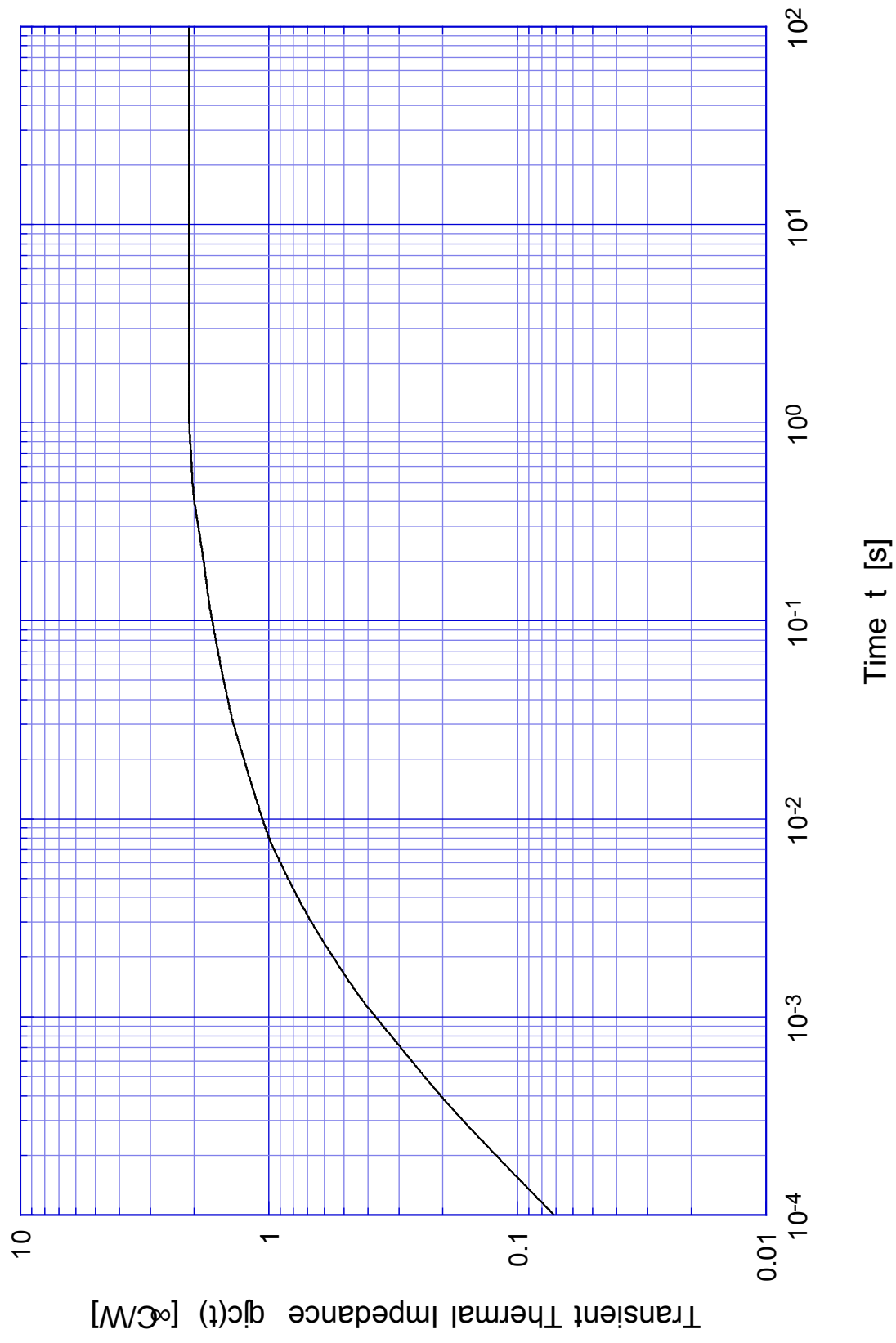


2SK2560

Safe Operating Area

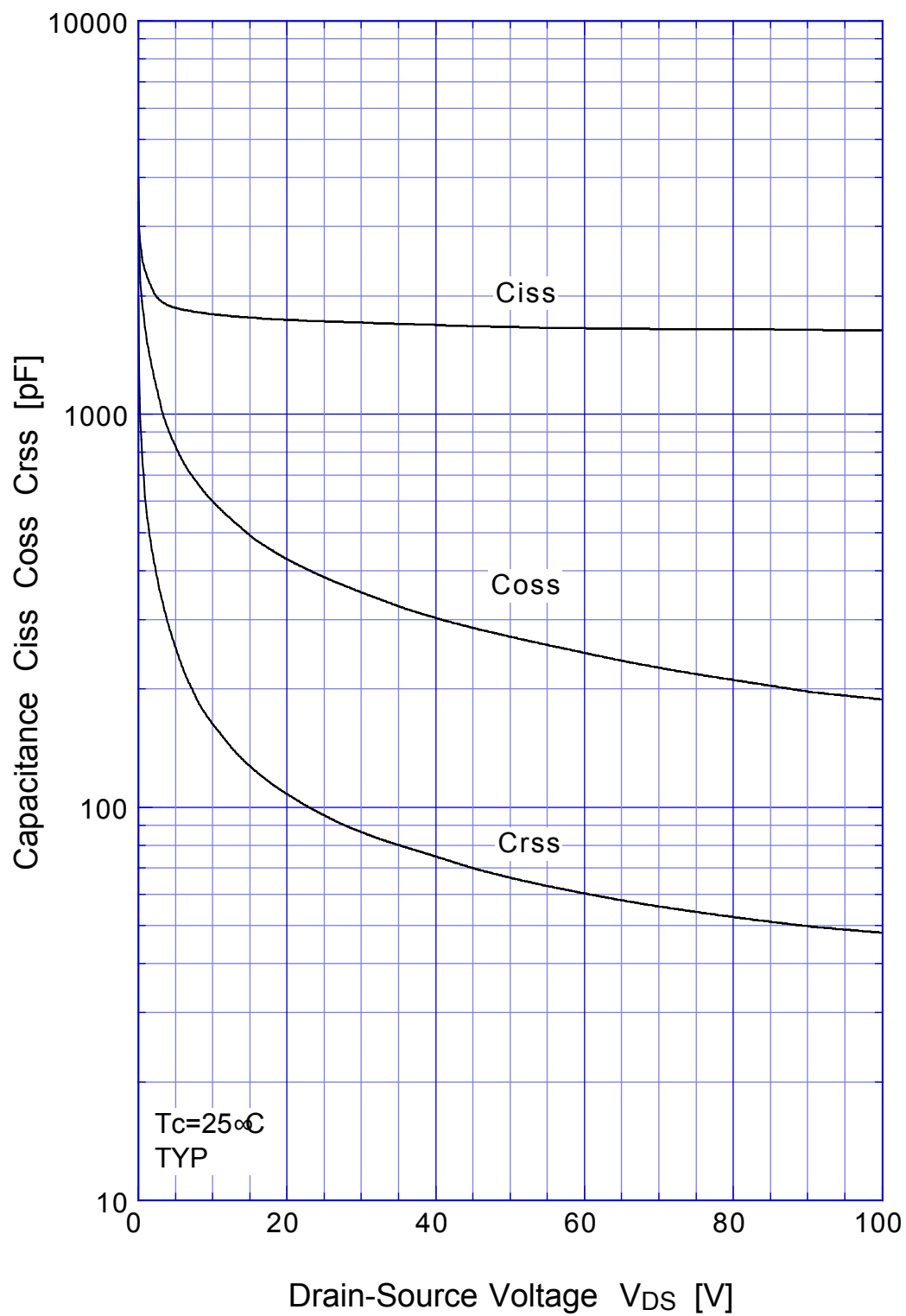


2SK2560 Transient Thermal Impedance



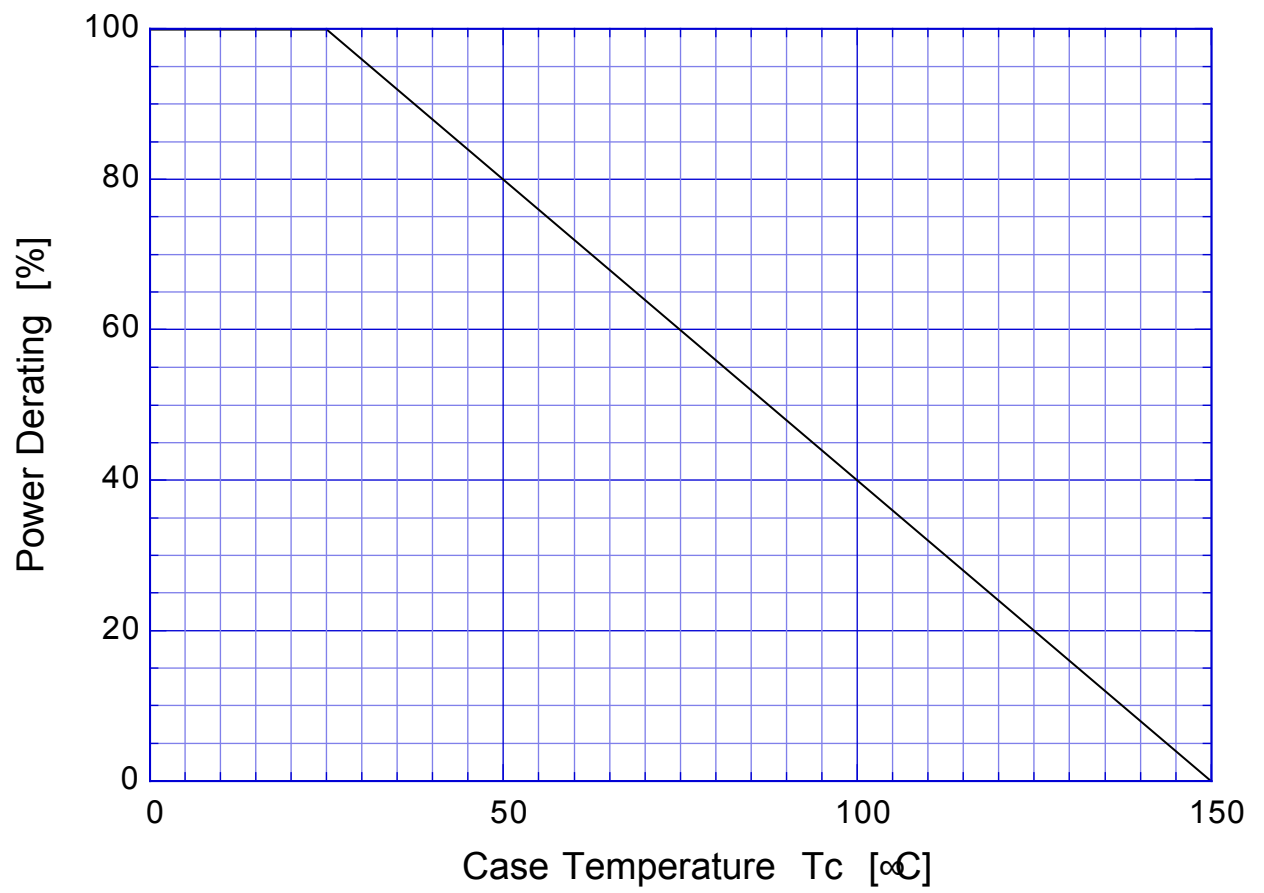
2SK2560

Capacitance



2SK2560

Power Derating



2SK2560

Gate Charge Characteristics

